

NJD2873T4G

Plastic Power Transistors

NPN Silicon DPAK For Surface Mount Applications

Designed for high-gain audio amplifier applications.

Features

- High DC Current Gain –
 $h_{FE} = 120$ (Min) @ $I_C = 500$ mA
 $= 40$ (Min) @ $I_C = 2$ A
- Low Collector–Emitter Saturation Voltage –
 $V_{CE(sat)} = 0.3$ Vdc (Max) @ $I_C = 1$ A
- High Current–Gain – Bandwidth Product –
 $f_T = 65$ MHz (Min) @ $I_C = 100$ mA
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings: Human Body Model, 3B > 8000 V
Machine Model, C > 400 V
- These are Pb–Free Packages

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Base Voltage	V_{CB}	50	Vdc
Collector–Emitter Voltage	V_{CEO}	50	Vdc
Emitter–Base Voltage	V_{EB}	5	Vdc
Collector Current	I_C	2 3	Adc
Base Current	I_B	0.4	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	15 0.1	W W/ $^\circ\text{C}$
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ * Derate above 25°C	P_D	1.68 0.011	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +175	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance	$R_{\theta JC}$	10	$^\circ\text{C}/\text{W}$
Junction–to–Case Junction–to–Ambient*	$R_{\theta JA}$	89.3	

*These ratings are applicable when surface mounted on the minimum pad sizes recommended.

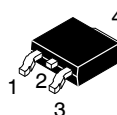


ON Semiconductor®

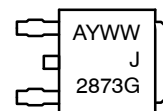
<http://onsemi.com>

**SILICON
POWER TRANSISTORS
2 AMPERES
50 VOLTS
15 WATTS**

MARKING DIAGRAM



DPAK
CASE 369C
STYLE 1



A = Assembly Location
Y = Year
WW = Work Week
G = Pb–Free Device

ORDERING INFORMATION

Device	Package	Shipping†
NJD2873T4G	DPAK (Pb–Free)	2500 Units / Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NJD2873T4G

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage (Note 1) (I _C = 10 mA _{dc} , I _B = 0)	V _{CEO(sus)}	50	–	V _{dc}
Collector Cutoff Current (V _{CB} = 50 V _{dc} , I _E = 0)	I _{CBO}	–	100	nA _{dc}
Emitter Cutoff Current (V _{BE} = 5 V _{dc} , I _C = 0)	I _{EBO}	–	100	nA _{dc}

ON CHARACTERISTICS

DC Current Gain (Note 1) (I _C = 0.5 A, V _{CE} = 2 V) (I _C = 2 A _{dc} , V _{CE} = 2 V _{dc}) (I _C = 0.75 A _{dc} , V _{CE} = 1.6 V _{dc} , –40°C ≤ T _J ≤ 150°C)	h _{FE}	120 40 80	360 – 360	–
Collector-Emitter Saturation Voltage (Note 1) (I _C = 1 A, I _B = 0.05 A)	V _{CE(sat)}	–	0.3	V _{dc}
Base-Emitter Saturation Voltage (Note 1) (I _C = 1 A, I _B = 0.05 A _{dc})	V _{BE(sat)}	–	1.2	V _{dc}
Base-Emitter On Voltage (Note 1) (I _C = 1 A _{dc} , V _{CE} = 2 V _{dc}) (I _C = 0.75 A _{dc} , V _{CE} = 1.6 V _{dc} , –40°C ≤ T _J ≤ 150°C)	V _{BE(on)}	– –	1.2 0.95	V _{dc}

DYNAMIC CHARACTERISTICS

Current-Gain – Bandwidth Product (Note 2) (I _C = 100 mA _{dc} , V _{CE} = 10 V _{dc} , f _{test} = 10 MHz)	f _T	65	–	MHz
Output Capacitance (V _{CB} = 10 V _{dc} , I _E = 0, f = 0.1 MHz)	C _{ob}	–	80	pF

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≈ 2%.
2. f_T = |h_{fe}| • f_{test}.

NJD2873T4G

TYPICAL CHARACTERISTICS

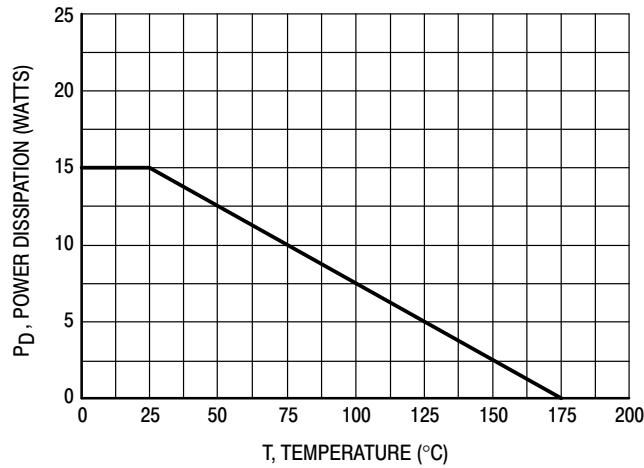


Figure 1. Power Derating

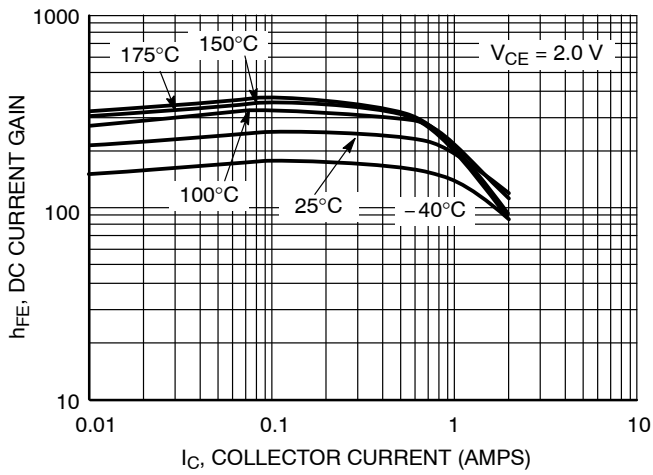


Figure 2. DC Current Gain

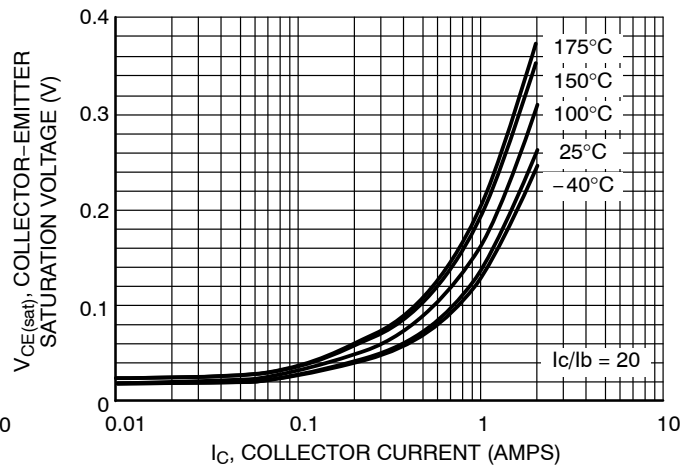


Figure 3. Collector-Emitter Saturation Voltage

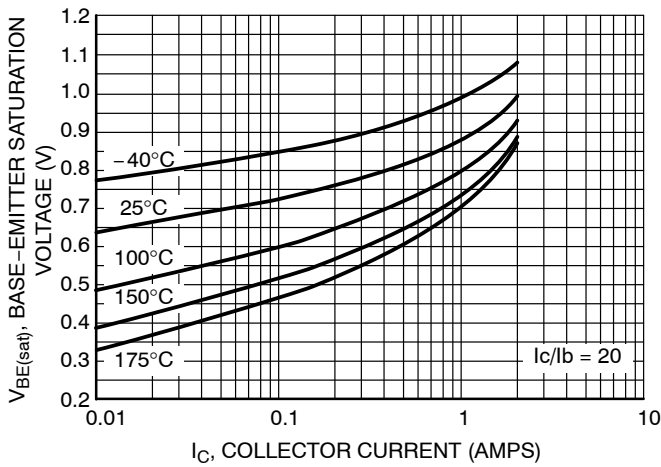


Figure 4. Base-Emitter Saturation Voltage

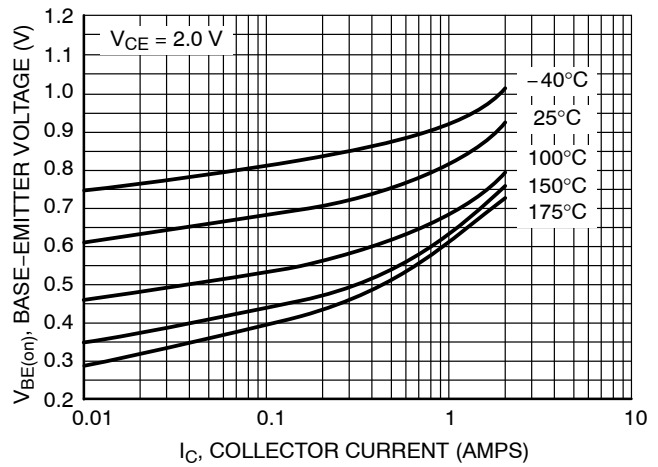


Figure 5. Base-Emitter Voltage

NJD2873T4G

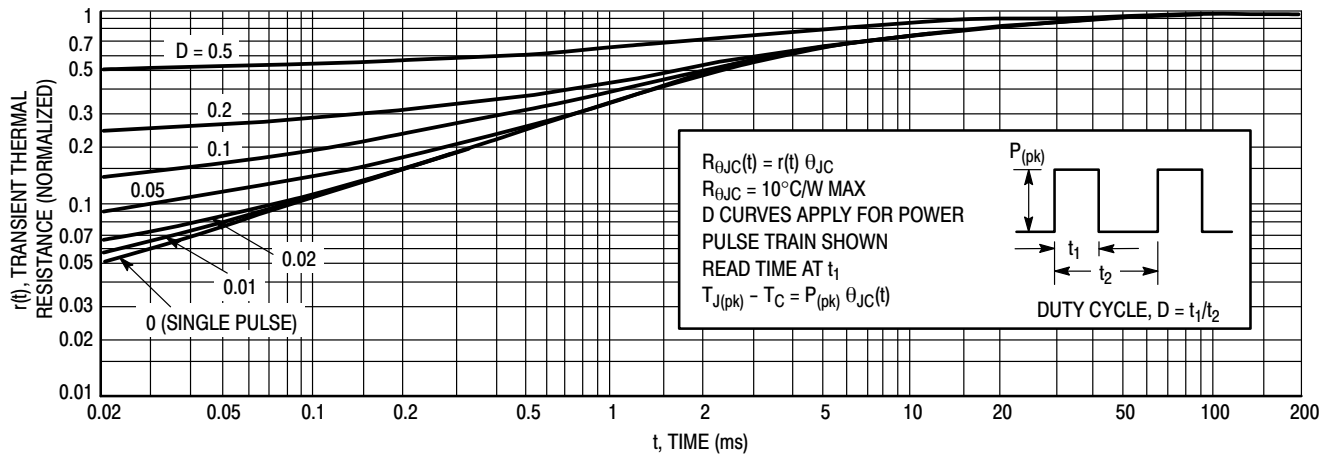
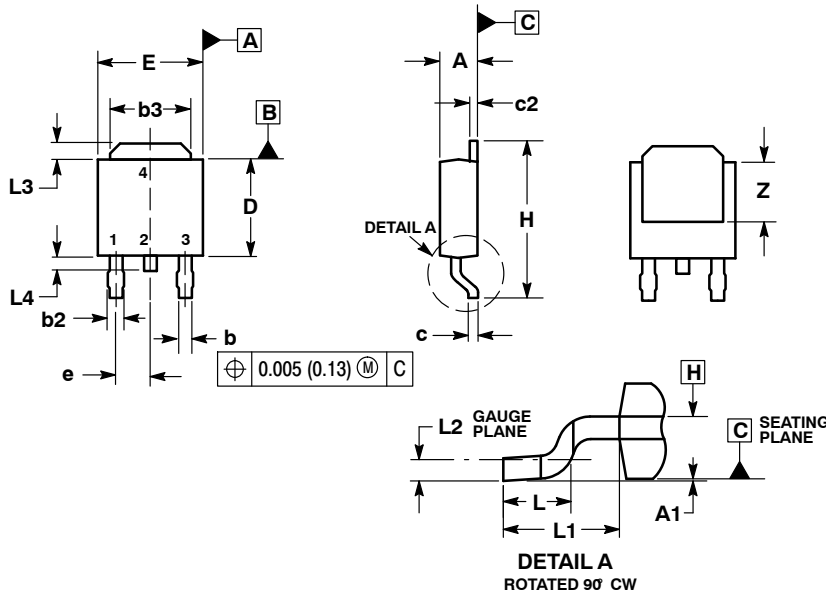


Figure 6. Thermal Response

NJD2873T4G

PACKAGE DIMENSIONS

DPAK CASE 369C-01 ISSUE D

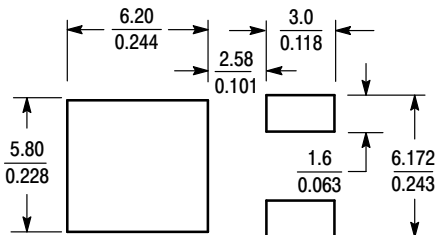


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

SOLDERING FOOTPRINT*



SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}} \right)$

STYLE 1:

- PIN 1. BASE
- COLLECTOR
- EMITTER
- COLLECTOR

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative